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	Applicant(s): Whonchee Lee et al.	
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U.S. PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	SubClass	Filing Date If Appropriate
VL		4,528,066	07/09/85	Merkling et al.	438	696	
VL		5,010,032	04/23/91	Tang et al.	438	228	
VL		5,047,367	09/10/91	Wei et al.	438	607	
VL		5,086,017	02/04/92	Lu	438	586	
VL		5,163,259	11/10/92	Kolar et al.	52	233	
VL		5,198,382	03/30/93	Campbell et al.	438	385	
VL		5,302,552	04/12/94	Duchateau et al.	438	664	
VL		5,482,895	01/09/96	Hayashi et al.	438	620	
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VL		5,567,651	10/22/96	Berti et al.	438	303	
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FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	SubClass	Translation Yes	Translation No
		NONE						

OTHER DOCUMENTS (Including Authors, Title, Date, Pertinent Papers, etc.)

VL			Goto et al., "Optimization of Salicide Processes for sub 0.1-μm CMOS Devices", 1994 Symposium on VLSI Technology Digest of Technical Papers, pgs. 119-120 (1994).
VL			Ohguro et al., "Nitrogen-doped nickel monosilicide technique for deep submicron CMOS salicide", International Electron Devices Meeting, Washington, D.C., December 10-13, 1995, pgs. 10.3.1-10.3.4.

EXAMINER	Date Considered
VL	12/26/00

*Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.